RF Power MOSFET Transistor 5W, 500-1000MHz, 28V

Features

- N-Channel enhancement mode device .
- DMOS structure
- Lower capacitances for broadband operation
- Common source configuration
- Lower noise floor
- Applications Broadband linear operation 500 MHz to 1400 MHz

ABSOLUTE MAXIMUM RATINGS AT 25° C

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V _{DS}	65	V
Gate-Source Voltage	V _{GS}	20	V
Drain-Source Current	I _{DS}	1.4	А
Power Dissipation	PD	14.4	W
Junction Temperature	TJ	200	°C
Storage Temperature	T _{STG}	-65 to +150	°C
Thermal Resistance	$\theta_{\rm JC}$	12.1	°C/W

TYPICAL DEVICE IMPEDANCE

F (MHz)	Z _{IN} (Ω)	Z _{LOAD} (Ω)			
500	4.3 - j29.0	27.3 +j28.6			
1000	2.2 - j2.75	8.0 + j16.0			
1400	2.8 - j3.0	9.4 + j10.6			
V_{DD} = 28V, I_{DQ} = 50 mA, P_{OUT} = 5.0 W					

Z_{IN} is the series equivalent input impedance of the device from gate to source.

ZLOAD is the optimum series equivalent load impedance as measured from drain to ground.

E

ELECTRICAL CHARACTERISTICS AT 25°C							
Parameter	Symbol	Min	Max	Units	Test Conditions		
Drain-Source Breakdown Voltage	BV_{DSS}	65	-	V	V_{GS} = 0.0 V , I_{DS} = 2.0 mA		
Drain-Source Leakage Current	I _{DSS}	-	1.0	mA	V_{GS} = 28.0 V , V_{GS} = 0.0 V		
Gate-Source Leakage Current	I _{GSS}	-	1.0	μA	V_{GS} = 20.0 V , V_{DS} = 0.0 V		
Gate Threshold Voltage	V _{GS(TH)}	2.0	6.0	V	V _{DS} = 10.0 V , I _{DS} = 10.0 mA		
Forward Transconductance	Gм	80	-	mS	V_{DS} = 10.0 V , I_{DS} 100.0 mA , ΔV_{GS} = 1.0V, 80 μs Pulse		
Input Capacitance	CISS	-	7	pF	V _{DS} = 28.0 V , F = 1.0 MHz		
Output Capacitance	C _{OSS}	-	5	pF	V _{DS} = 28.0 V , F = 1.0 MHz		
Reverse Capacitance	C_{RSS}	-	2.4	pF	V _{DS} = 28.0 V , F = 1.0 MHz		
Power Gain	G _P	10	-	dB	V_{DD} = 28.0 V, $~I_{\text{DQ}}$ = 50 mA, P_{OUT} = 5.0 W, F =1.0 GHz		
Drain Efficiency	ŋ₀	50	-	%	V_{DD} = 28.0 V, $~I_{\text{DQ}}$ = 50 mA, P_{OUT} = 5.0 W, F =1.0 GHz		
Load Mismatch Tolerance	VSWR-T	-	20:1	-	V_{DD} = 28.0 V, I _{DQ} = 50 mA, P _{OUT} = 5.0 W, F =1.0 GHz		

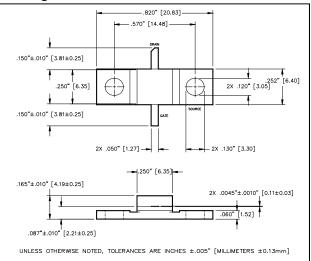
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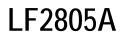
LETTER	MILLIM	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
A	20.70	20.96	.815	.825	
В	14.35	14.61	.565	.575	
С	13.72	14.22	.540	.560	
D	6.27	6.53	.247	.257	
E	6.22	6.48	.245	.255	
F	6.22	6.48	.245	.255	
G	1.14	1.40	.045	.055	
н	2.92	3.18	.115	.125	
J	1.40	1.65	.055	.065	
к	1.96	2.46	.077	.097	
L	3.61	4.37	.142	.172	
М	.08	.15	.003	.006	



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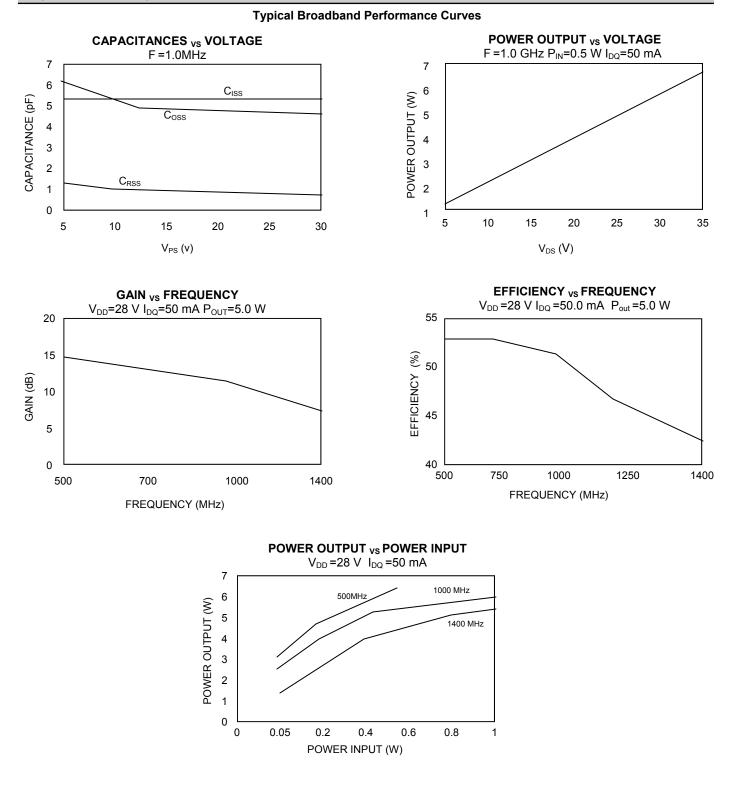
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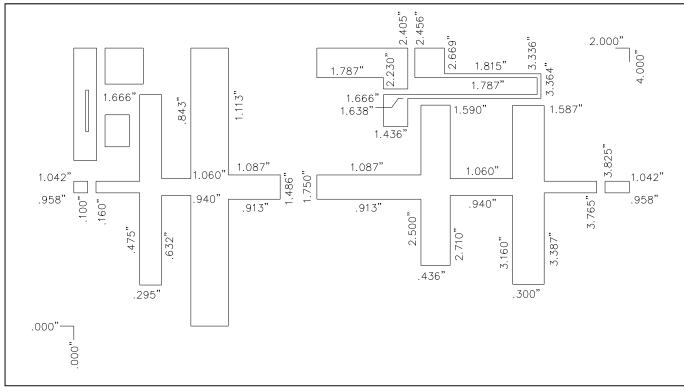
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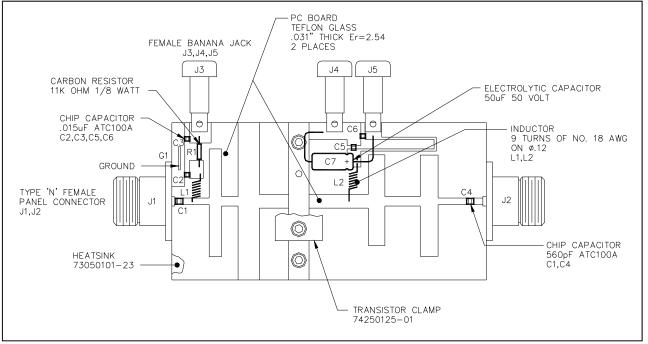
TEST FIXTURE CIRCUIT DIMENSIONS

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TEST FIXTURE ASSEMBLY



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